

## T2035H

双向可控硅  
TRIAC版本号  
201603-A

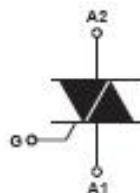
## 产品概述 GENERAL DESCRIPTION

T2035H 双向可控硅采用穿通隔离台面结构，复合玻璃钝化PN结表面保护工艺技术，dv/dt高，可靠性高，适用于控温、调光、马达控制。

T2035H Triacs is fabricated using separation diffusion processes ,the junction termination areas are passivated with glass. Thanks to highly dv/dt and reliability,the Triacs series is suitable for domestic lighting ,heating and motor speed controllers.

## 主要参数 MAIN CHARACTERISTICS

参数 Parameter	数值 Value	单位 Unit
I <sub>T</sub> (RMS)	20	A
V <sub>DRM/V<sub>RRM</sub></sub>	800	V
I <sub>GT</sub>	≤35	mA



TO-220A

## 产品特性 FEATURES

- dv/dt高
- 通态压降低
- RoHS环保产品
- Highly dv/dt
- Low on-state voltage
- RoHS Products

## 应用领域 APPLICATIONS

主要应用于调光、控温、马达控制。

domestic lighting ,heating and motor speed controllers.

## 极限值(除非另有规定, $T_j=25^\circ\text{C}$ ) ABSOLUTE RATINGS

( $T_j=25^\circ\text{C}$ ,unless otherwise specified)

符号 Symbol	参数 Parameter		数值 Value	单位 Unit
$I_{TRMS}$	RMS 通态电流 RMS on-state current (full sine wave)	$T_c=105^\circ\text{C}$	20	A
$I_{TSM}$	通态峰值浪涌电流 Non repetitive surge peak on-state current	$F=50\text{Hz}, t=20\text{ms}$	210	A
$I^2t$	$I^2t$ 耗散值 $I^2t$ value for fusing	$T_p=10\text{ms}$	200	$\text{A}^2\text{s}$
$di/dt$	通态电流上升值 Critical rate of rise of on-state current	$F=120\text{Hz}, T_j=125^\circ\text{C}$	50	$\text{A}/\mu\text{s}$
$I_{GM}$	门极峰值电流 Peak gate current	$TP=20\mu\text{s}, T_j=125^\circ\text{C}$	4	A
$P_{G(AV)}$	平均门极耗散功率 Average gate power dissipation	$T_j=125^\circ\text{C}$	1	W
$T_{stg}$	贮存结温范围 Storage junction temperature range		-40~+150	°C
$T_j$	工作结温范围 Operating junction temperature range		-40~+150	°C

## 电参数(除非另有规定, $T_j=25^\circ\text{C}$ ) ELECTRICAL CHARACTERISTICS

( $T_j=25^\circ\text{C}$ ,unless otherwise specified)

参数 Parameter	符号 Symbol	规范值 Value	单位 Unit	测试条件 Test Conditions
触发电流 Gate trigger current	$I_{GT}$	$I \sim III$	$\leq 35$	$\text{mA}$ $V_D=12\text{V}, I_T=0.1\text{A}$
触发电压 Gate trigger voltage	$V_{GT}$	$I \sim III$	$\leq 1.5$	$\text{V}$ $V_D=12\text{V}, I_T=0.1\text{A}$
维持电流 Holding current	$I_H$	$\leq 50$	$\text{mA}$	$V_D=12\text{V}, I_T=0.1\text{A}$
擎住电流 Latching current	$I_L$	$\leq 80$	$\text{mA}$	$V_D=12\text{V}, I_T=0.1\text{A}$
电压上升率 Rise of off- state voltage	$dv/dt$	$\geq 200$	$\text{V}/\mu\text{s}$	$V_D=67\%V_{DRM}$
通态压降 Peak on-state voltage	$V_{TM}$	$\leq 1.7$	$\text{V}$	$I_T=28\text{A}$
断态漏电流 Peak repetitive forward blocking current	$I_{DRM}$ $I_{RRM}$	$\leq 10$ $\leq 4$	$\mu\text{A}$ $\text{mA}$	$V_{RRM}=V_{DRM}, T_j = 25^\circ\text{C}$ $V_{RRM}=V_{DRM}, T_j = 150^\circ\text{C}$

## 热特性 THERMAL RESISTANCES

符号 Symbol	参数 Parameter	数值 Value	单位 Unit
$R_{th(j-c)}$	Junction to case(AC)	1.3	°C/W
$R_{th(j-a)}$	Junction to ambient	60	°C/W

## 特征曲线 ELECTRICAL CHARACTERISTICS (CURVES)

图1 最大耗散功率与RMS通态电流关系

Fig.1. Maximum Power Dissipation Versus  
on-state current

图2 RMS通态电流与T<sub>c</sub>温度关系

Fig.2. RMS On-state Current Versus T<sub>L</sub>

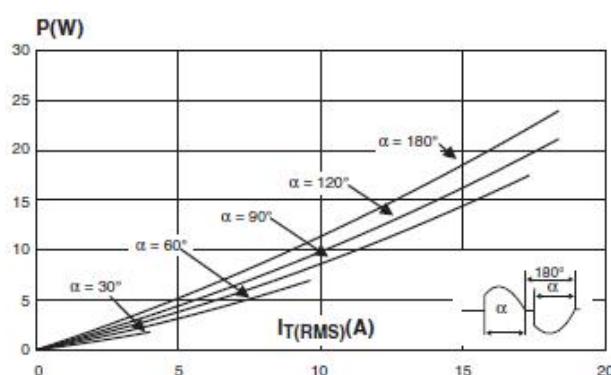


图3 通态特性

Fig.3. On-State Characteristics

I<sub>T</sub>(RMS) (A)

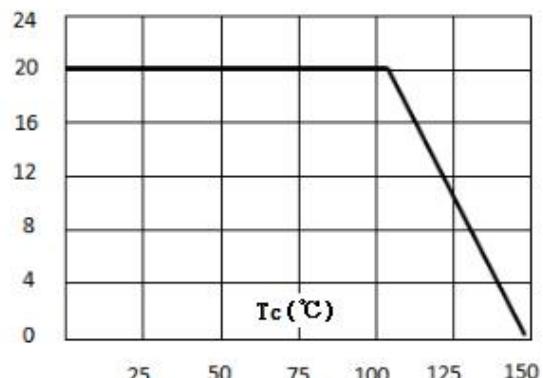
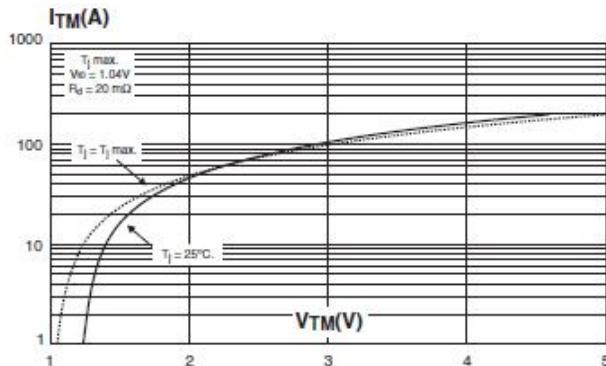


图4 通态浪涌峰值电流与周期数关系

Fig.4. Surge Peak On-state Current Versus Number Cycles



I<sub>TSM</sub>(A)

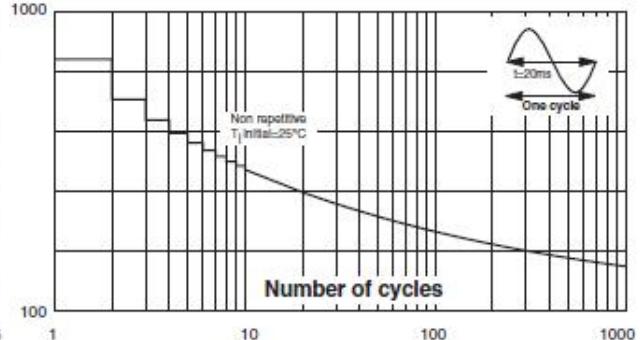
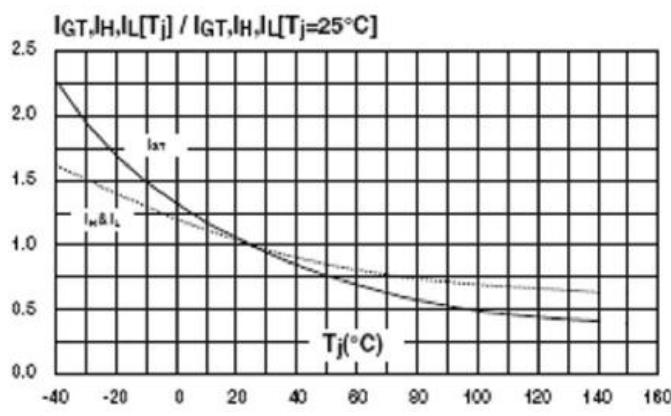
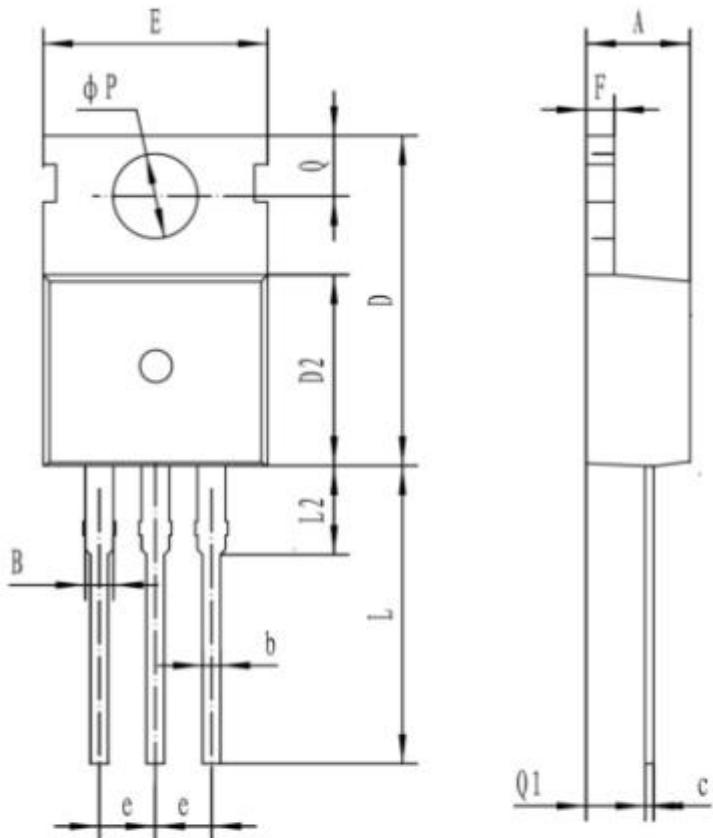


图5 I<sub>GT</sub>、I<sub>H</sub>、I<sub>L</sub>相对值（相对于25℃）与结温关系

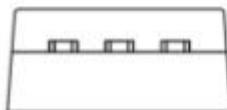
Fig.5. Relative Variation Of Gate Trigger Current

, Holding Current And Latching Current Versus Junction Temperature (Typical Value)



**封装尺寸 PACKAGE MECHANICAL DATA**
**TO-220A**


符号 symbol	MIN	MAX
A	4.30	4.70
B	1.10	1.40
b	0.70	0.95
c	0.40	0.65
D	15.20	16.20
D2	9.00	9.40
E	9.70	10.10
e	2.39	2.69
F	1.25	1.40
L	12.60	13.60
L2	2.80	3.20
Q	2.60	3.00
Q1	2.20	2.60
P	3.50	3.80



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